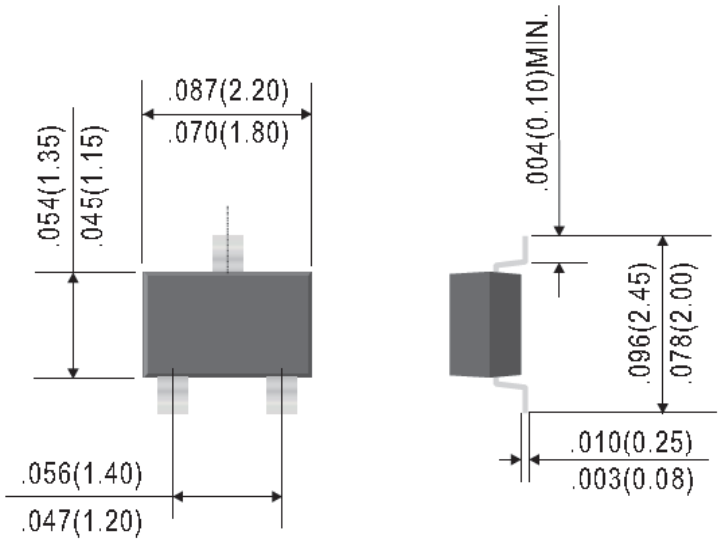
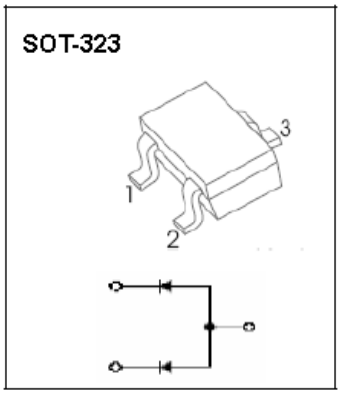
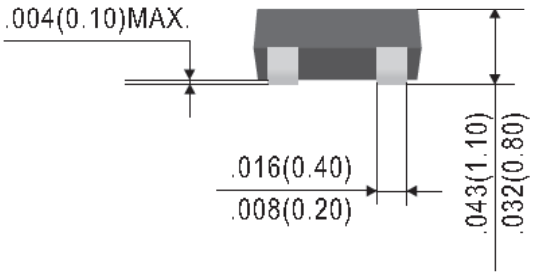
DAP202U

Plastic-Encapsulate Diodes







Dimensions in inches and (millimeters)

FEATURES

·Four types of packaging are available
·High speed. (t_{rr}=1.5ns Typ.)
·Suitable for high packing density layout
·High reliability
·Pb-Free package is available
·RoHS product for packing code suffix "G"
·Halogen free product for packing code suffix "H"
·Moisture Sensitivity Level 1

MARKING: **P**

DAP202U

Plastic-Encapsulate Diodes

Maximum Ratings (T_a=25°C unless otherwise noted)			
Parameter	**Symbol**	**Limit**	**Unit**
Peak reverse voltage	V_{RM}	80	V
DC Blocking Voltage	V_R	80	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Forward Current	I_O	100	mA
Power Dissipation	P_D	200	mW
Junction temperature	T_J	150	°C
Operating/ Storage Temperature Range	T_{STG}	-55~+150	°C

Electrical Characteristics (T_a=25°C unless otherwise noted)						
Parameter	**Symbol**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Reverse Voltage	$V_{(BR)}$	I_R= 100μA	80	—	—	V
Forward Voltage	V_F	I_F=100mA	—	—	1.2	V
Reverse Current	I_R	V_R=70V	—	—	0.1	μA
Diode Capacitance	C_D	V_R=6V, f=1MHz	—	—	3.5	pF
Reverse Recovery Time	t_{rr}	V_R=6V, I_F=5mA	—	—	4	ns

Typical Characteristics

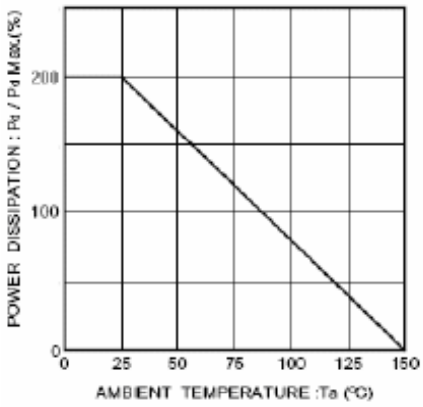


Fig.1 Power attenuation curve

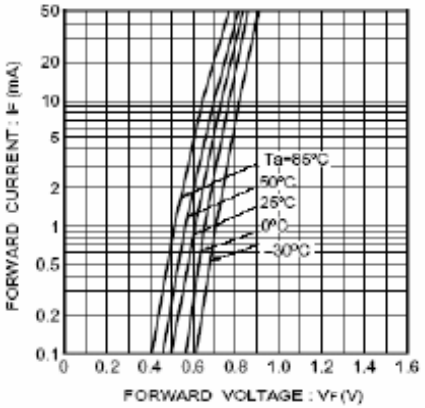


Fig.2 Forward characteristics (P Type)

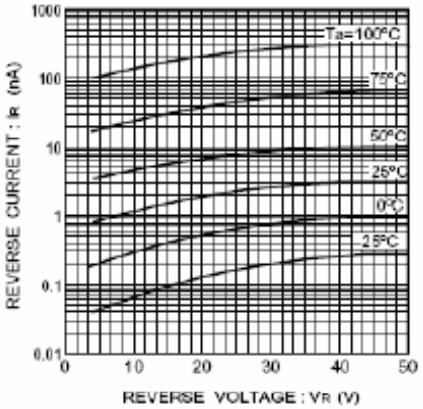


Fig.3 Reverse characteristics (P Type)

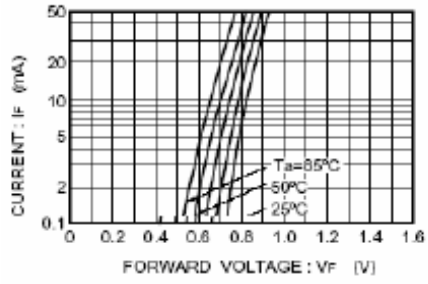


Fig.4 Forward characteristics (N Type)

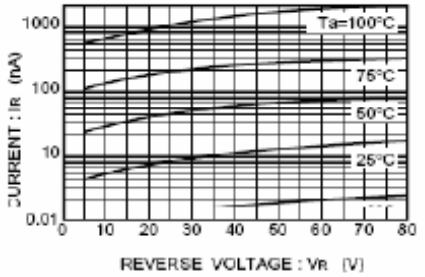


Fig.5 Reverse characteristics (N Type)

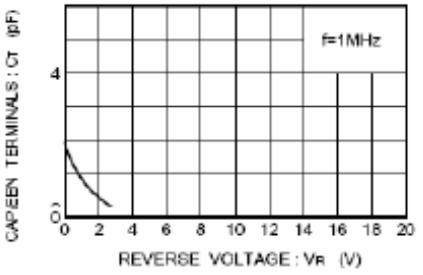


Fig.6 Capacitance between terminals characteristics

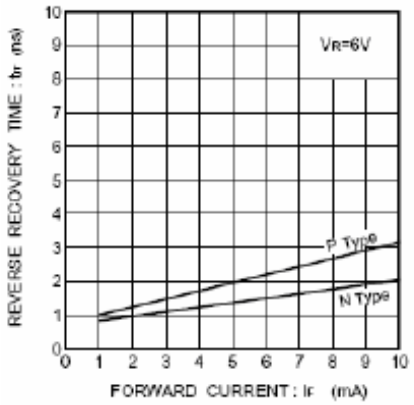


Fig.7 Reverse recovery time

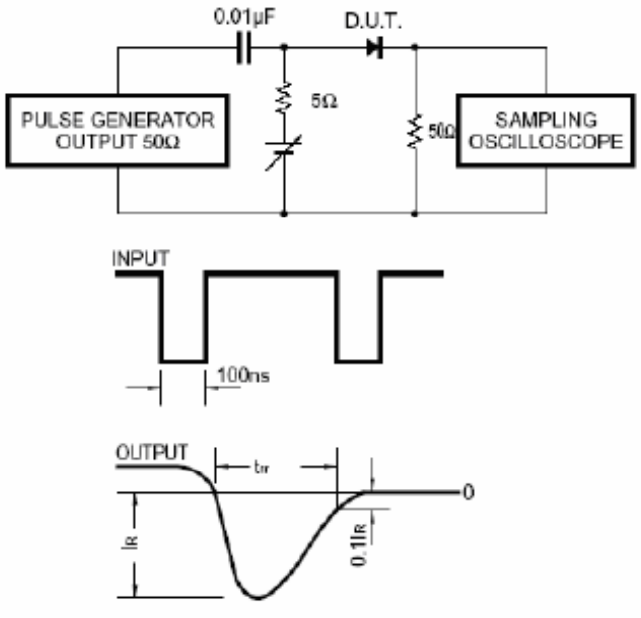


Fig.8 Reverse recovery time (t_{rr}) measurement circuit